

# Nikita Yu Gordeev

## List of Publications by Year in descending order

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22  
papers

389  
citations

840776

11  
h-index

839539

18  
g-index

22  
all docs

22  
docs citations

22  
times ranked

193  
citing authors

#	ARTICLE	IF	CITATIONS
1	Negative Characteristic Temperature of InGaAs Quantum Dot Injection Laser. Japanese Journal of Applied Physics, 1997, 36, 4216-4218.	1.5	94
2	InGaAs/GaAs Quantum Dot Lasers with Ultrahigh Characteristic Temperature ( $T_0=385\text{K}$ ) Grown by Metal Organic Chemical Vapour Deposition. Japanese Journal of Applied Physics, 1997, 36, 4221-4223.	1.5	60
3	Transverse single-mode edge-emitting lasers based on coupled waveguides. Optics Letters, 2015, 40, 2150.	3.3	40
4	Light Emitting Devices Based on Quantum Well-Dots. Applied Sciences (Switzerland), 2020, 10, 1038.	2.5	37
5	Multi-Stacked InAs/InGaAs/InP Quantum Dot Laser ( $J_{th}=11\text{A}/\text{cm}^2$ , $\lambda=1.9\mu\text{m}$ (77 K)). Japanese Journal of Applied Physics, 1999, 38, 601-604.	1.5	30
6	High-Power Low-Beam Divergence Edge-Emitting Semiconductor Lasers with 1- and 2-D Photonic Bandgap Crystal Waveguide. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1113-1122.	2.9	27
7	Tilted Wave Lasers: A Way to High Brightness Sources of Light. IEEE Journal of Quantum Electronics, 2011, 47, 1014-1027.	1.9	22
8	Vertically Coupled Quantum Dot Lasers: First Device Oriented Structures with High Internal Quantum Efficiency. Japanese Journal of Applied Physics, 1997, 36, 4219-4220.	1.5	15
9	Material gain of InGaAs/GaAs quantum well-dots. Semiconductor Science and Technology, 2021, 36, 015008.	2.0	14
10	Tunable electro-optic polarization modulator for quantum key distribution applications. Optics Communications, 2004, 234, 203-210.	2.1	12
11	Low divergence edge-emitting laser with asymmetric waveguide based on one-dimensional photonic crystal. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 919-922.	0.8	12
12	Collective Resonance and Form-Factor of Homogeneous Broadening in Semiconductors. Japanese Journal of Applied Physics, 1999, 38, 4772-4774.	1.5	3
13	Bipolar charging in quantum dots array. AIP Conference Proceedings, 2007, , .	0.4	3
14	Modeling of photonic-crystal-based high-power high-brightness semiconductor lasers. , 2010, , .		3
15	Fundamental transverse mode selection and self-stabilization in large optical cavity diode lasers under high injection current densities. Semiconductor Science and Technology, 2015, 30, 115007.	2.0	3
16	Study of waveguide absorption in InGaAs "quantum well-dots" heterostructures. Nano Structures Nano Objects, 2021, 25, 100628.	3.5	3
17	Thermally stable surface-emitting tilted wave laser. , 2018, , .		3
18	Improvement of thermal resistance in InGaAs/GaAs/AlGaAs microdisk lasers bonded onto silicon. Semiconductor Science and Technology, 2022, 37, 075010.	2.0	3

#	ARTICLE	IF	CITATIONS
19	Single-Lobe Single-Wavelength Lasing in Ultrabroad-Area Vertical-Cavity Surface-Emitting Lasers Based on the Integrated Filter Concept. IEEE Journal of Quantum Electronics, 2008, 44, 724-731.	1.9	2
20	Refractive index of laser active region based on InAs/InGaAs quantum dots. Journal of Nanophotonics, 2013, 7, 073087.	1.0	2
21	Optoelectronic devices with active region based on InGaAs/GaAs quantum well dots. , 2020, , .		1
22	Temperature characteristics of tilted wave lasers. Optical Engineering, 2016, 55, 116102.	1.0	0